

# NUF6406MN

## Low Capacitance 6 Line EMI Filter with ESD Protection

This device is a 6 line EMI filter array for wireless applications. Greater than -30 dB attenuation is obtained at frequencies from 800 MHz to 2.4 GHz. It also offers ESD protection—clamping transients from static discharges. ESD protection is provided across all capacitors.

### Features

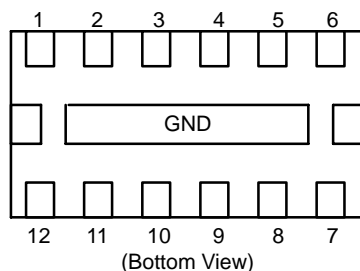
- EMI Filtering and ESD Protection
- Integration of 30 Discrete Components
- Compliance with IEC61000-4-2 (Level 4)  
> 8.0 kV (Contact)
- DFN Package, 1.35 x 3.0 mm
- Moisture Sensitivity Level 1
- ESD Ratings: Machine Model = C  
Human Body Model = 3B
- This is a Pb-Free Device\*

### Benefits

- Reduces EMI/RFI Emissions on a Data Line
- Integrated Solution Offers Cost and Space Savings in a DFN Package
- Reduces Parasitic Inductances Which Offer a More “Ideal” Low Pass Filter Response
- Integrated Solution Improves System Reliability
- Compatible Footprint to BGA or Flip-Chip Package

### Applications

- EMI Filtering and ESD Protection for Data Lines
- Wireless Phones
- PDAs and Handheld Products
- Notebook Computers
- LCD Displays



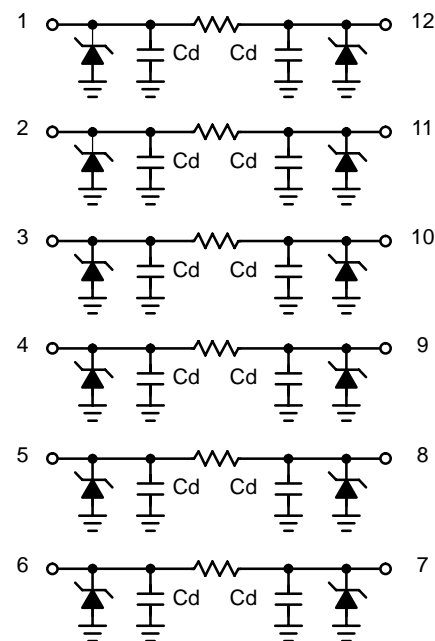
(Bottom View)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

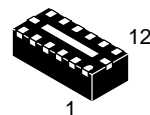


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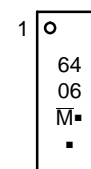


(Top View)



DFN12  
CASE 506AD

### MARKING DIAGRAM



6406 = Specific Device Code  
M = Month  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NUF6406MNT1G	DFN12 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
ESD Discharge IEC61000-4-2 Contact Discharge	$V_{PP}$	8.0	kV
Operating Temperature Range	$T_{OP}$	-40 to 85	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes (1.8 in from case for 10 seconds)	$T_L$	260	$^\circ\text{C}$

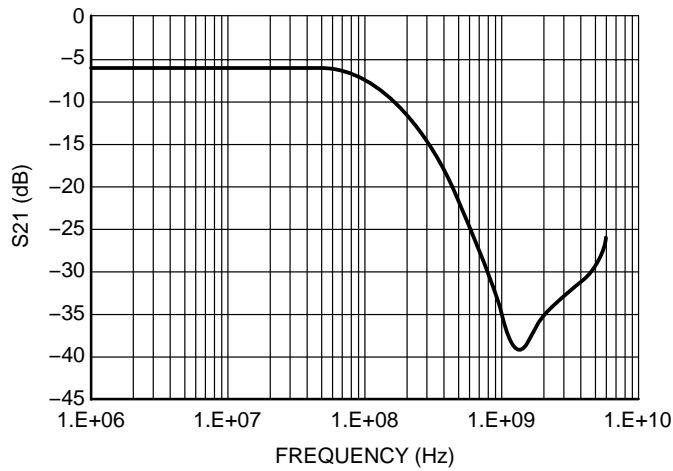
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

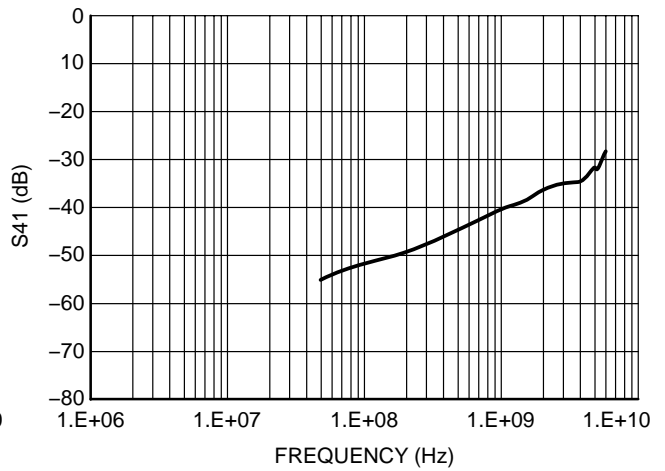
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Reverse Working Voltage	$V_{RWM}$				5.0	V
Breakdown Voltage	$V_{BR}$	$I_R = 1.0\text{ mA}$	6.0	7.0		V
Leakage Current	$I_R$	$V_{RWM} = 3.0\text{ V}$			1.0	$\mu\text{A}$
Resistance	$R_A$	$I_R = 20\text{ mA}$	85	100	115	$\Omega$
Capacitance (Notes 1 and 2)	$C_d$	$V_R = 2.5\text{ V}$ , $f = 1.0\text{ MHz}$		13	16	pF
Cut-Off Frequency (Note 3)	$f_{3dB}$	Above this frequency, appreciable attenuation occurs		138		MHz

1. Measured at  $25^\circ\text{C}$ ,  $V_R = 2.5\text{ V}$ ,  $f = 1.0\text{ MHz}$ .
2. Total line capacitance is 2 times the Diode Capacitance ( $C_d$ ).
3.  $50\ \Omega$  source and  $50\ \Omega$  load termination.

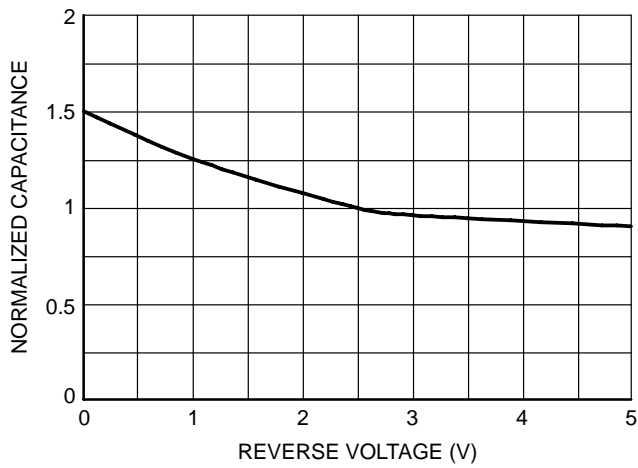
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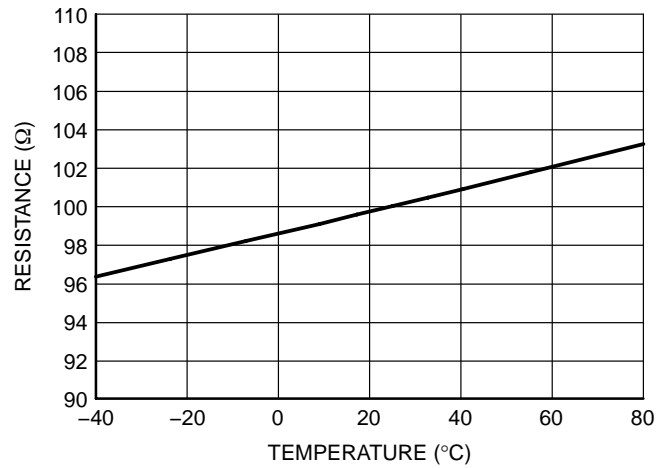
**Figure 1. Insertion Loss Characteristic**



**Figure 2. Analog Crosstalk**



**Figure 3. Typical Capacitance vs. Reverse Biased Voltage  
(Normalized Capacitance, Cd @ 2.5 V)**



**Figure 4. Typical Resistance over Temperature**

